

# DMG964H1

Silicon NPN epitaxial planar type (Tr1)  
 Silicon PNP epitaxial planar type (Tr2)

For digital circuits

■ Features

- Low collector-emitter saturation voltage  $V_{CE(sat)}$
- Contributes to miniaturization of sets, reduction of component count.
- Eco-friendly Halogen-free package

■ Basic Part Number

DRC2144E + DRA2143X (Individual)

■ Packaging

DMG964H10R Embossed type (Thermo-compression sealing): 8000 pcs / reel (standard)

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$

	Parameter	Symbol	Rating	Unit
Tr1	Collector-base voltage (Emitter open)	$V_{CBO}$	50	V
	Collector-emitter voltage (Base open)	$V_{CEO}$	50	V
	Collector current	$I_C$	100	mA
Tr2	Collector-base voltage (Emitter open)	$V_{CBO}$	-50	V
	Collector-emitter voltage (Base open)	$V_{CEO}$	-50	V
	Collector current	$I_C$	-100	mA
Overall	Total power dissipation	$P_T$	125	mW
	Junction temperature	$T_j$	150	$^\circ\text{C}$
	Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

■ Package

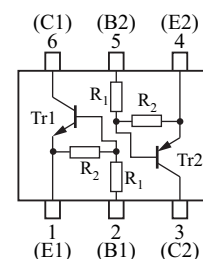
- Code  
SSMini6-F3-B  
Package dimension clicks here.→

• Pin Name

- 1: Emitter (Tr1)      4: Emitter (Tr2)
- 2: Base (Tr1)        5: Base (Tr2)
- 3: Collector (Tr2)    6: Collector (Tr1)

■ Marking Symbol: T2

■ Internal Connection



Resistance value	Tr1	$R_1$	47	k $\Omega$
		$R_2$	47	
	Tr2	$R_1$	4.7	k $\Omega$
		$R_2$	10	

■ Electrical Characteristics  $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

- Tr1

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	$I_C = 10 \mu\text{A}, I_E = 0$	50			V
Collector-emitter voltage (Base open)	$V_{CEO}$	$I_C = 2 \text{mA}, I_B = 0$	50			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 50 \text{V}, I_E = 0$			0.1	$\mu\text{A}$
Collector-emitter cutoff current (Base open)	$I_{CEO}$	$V_{CE} = 50 \text{V}, I_B = 0$			0.5	$\mu\text{A}$
Emitter-base cutoff current (Collector open)	$I_{EBO}$	$V_{EB} = 6 \text{V}, I_C = 0$			0.1	mA
Forward current transfer ratio	$h_{FE}$	$V_{CE} = 10 \text{V}, I_C = 5 \text{mA}$	80			—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 10 \text{mA}, I_B = 0.5 \text{mA}$			0.25	V
Input voltage (ON)	$V_{I(on)}$	$V_{CE} = 0.2 \text{V}, I_C = 5 \text{mA}$	3.6			V
Input voltage (OFF)	$V_{I(off)}$	$V_{CE} = 5 \text{V}, I_C = 100 \mu\text{A}$			0.8	V
Input resistance	$R_1$		-30%	47	+30%	k $\Omega$
Resistance ratio	$R_1 / R_2$		0.8	1.0	1.2	—

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

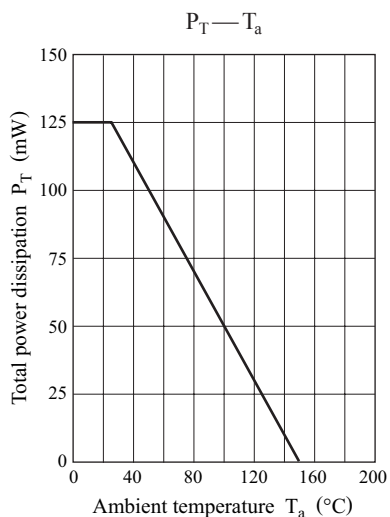
■ Electrical Characteristics (Continued)  $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

• Tr2

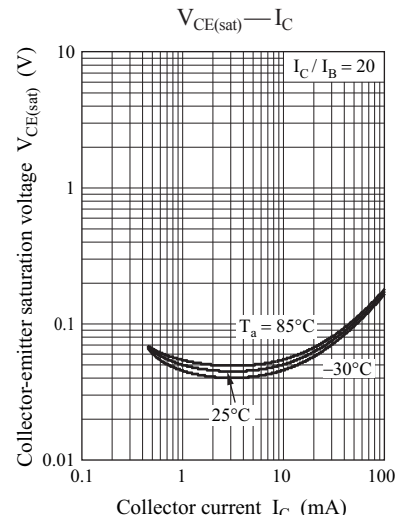
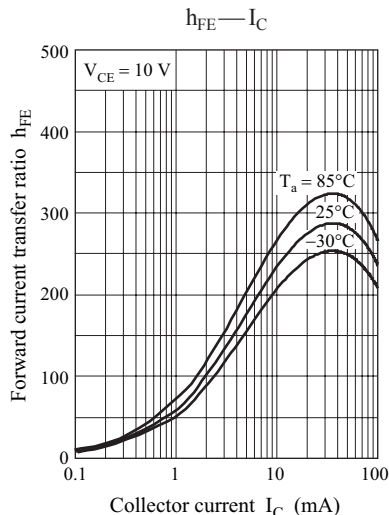
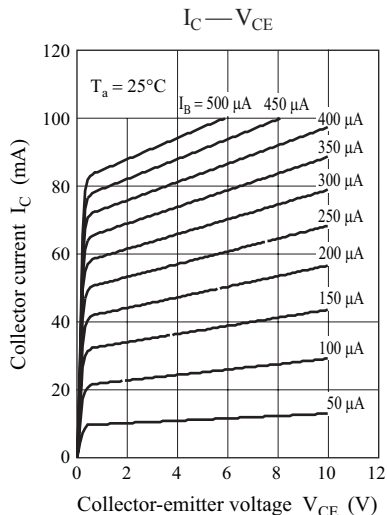
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	$I_C = -10 \mu\text{A}, I_E = 0$	-50			V
Collector-emitter voltage (Base open)	$V_{CEO}$	$I_C = -2 \text{mA}, I_B = 0$	-50			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = -50 \text{V}, I_E = 0$			-0.1	$\mu\text{A}$
Collector-emitter cutoff current (Base open)	$I_{CEO}$	$V_{CE} = -50 \text{V}, I_B = 0$			-0.5	$\mu\text{A}$
Emitter-base cutoff current (Collector open)	$I_{EBO}$	$V_{EB} = -6 \text{V}, I_C = 0$			-1.0	mA
Forward current transfer ratio	$h_{FE}$	$V_{CE} = -10 \text{V}, I_C = -5 \text{mA}$	30			—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -10 \text{mA}, I_B = -0.5 \text{mA}$			-0.25	V
Input voltage (ON)	$V_{I(on)}$	$V_{CE} = -0.2 \text{V}, I_C = -5 \text{mA}$	-1.7			V
Input voltage (OFF)	$V_{I(off)}$	$V_{CE} = -5 \text{V}, I_C = -100 \mu\text{A}$			-0.6	V
Input resistance	$R_1$		-30%	4.7	+30%	$\text{k}\Omega$
Resistance ratio	$R_1 / R_2$		0.37	0.47	0.57	—

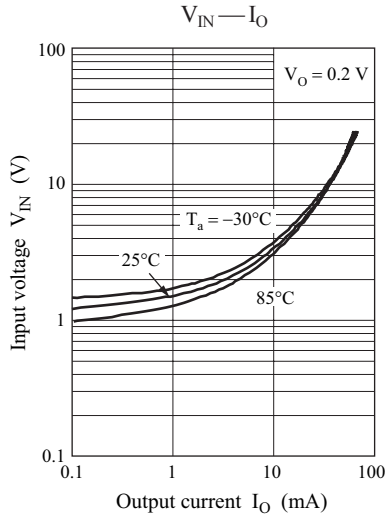
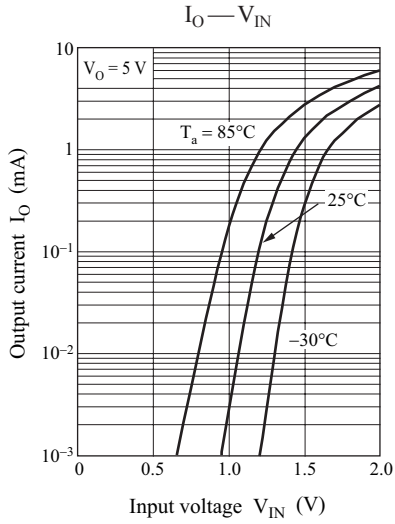
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

Common characteristics chart

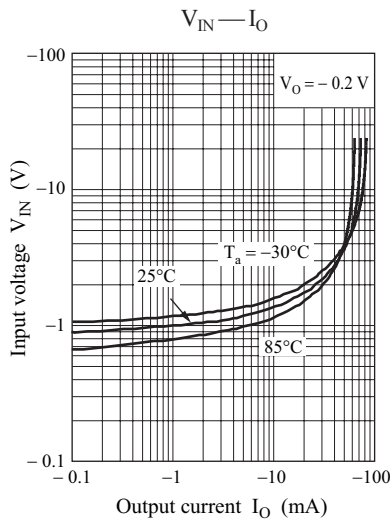
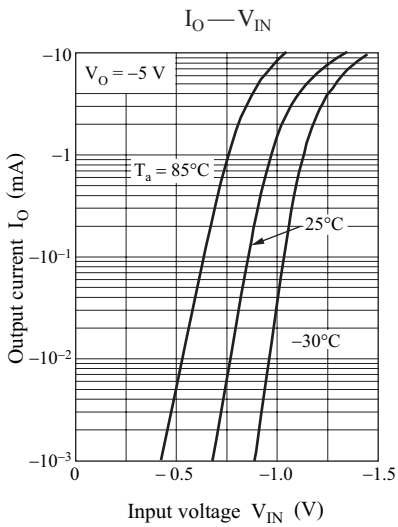
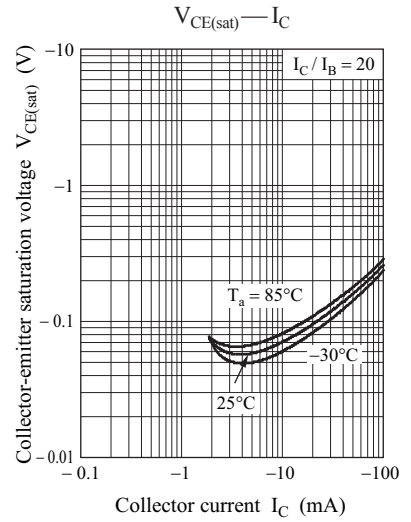
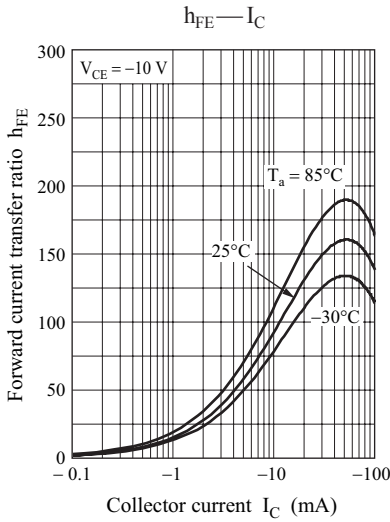
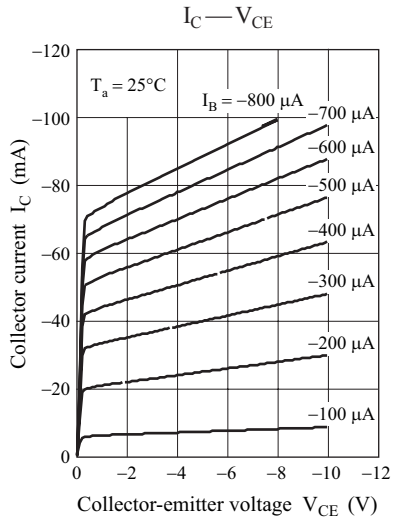


Characteristics charts of Tr1





Characteristics charts of Tr2



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